

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|---|------------------|---------|---------------------|
| L1 | 1 | 10/707084 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 15:52 |
| L2 | 42 | (US-20030218183-\$ or US-20030146444-\$ or US-20050012113-\$ or US-20020074553-\$ or US-20040080010-\$ or US-20030062525-\$ or US-20030015708-\$ or US-20020155634-\$ or US-20050167680-\$ or US-20060199289-\$ or US-20060226417-\$ or US-20050274964-\$ or US-20050082543-\$ or US-20050167697-\$ or US-20040124435-\$ or US-20030127658-\$ or US-20030071276-\$ or US-20020096687-\$ or US-20030214807-\$ or US-20030047744-\$ or US-20030122147-\$).did. or (US- 6429467-\$ or US- 6208074-\$ or US- 5717235-\$ or US- 5977565-\$ or US- 5673220-\$ or US- 5932905-\$ or US- 5507881-\$ or US- 5707887-\$ or US- 5847397-\$ or US- 5677538-\$ or US- 5598014-\$ or US- 6586272-\$ or US- 6495852-\$ or US- 6455340-\$ or US- 7151281-\$).did. or (JP-06216404-\$).did. or (US-20050012113-\$ or US-20030230235-\$ or EP-296371-\$ or US-20050032345-\$ or JP-06216404-\$).did. | US-PGPUB; USPAT; JPO; DERWENT | OR | ON | 2008/03/10 16:06 |

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|-----|-----|--|---|----|----|---------------------|
| L3 | 18 | I2 and schottky | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:06 |
| L4 | 0 | I2 and (schottky near10 biased) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:07 |
| L5 | 5 | I2 and (schottky near10 (bias or biasing or biased)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:07 |
| L6 | 5 | I2 and (schottky with (bias or biasing or biased)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:07 |
| L7 | 6 | I2 and (schottky with (reverse or bias or biasing or biased)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:08 |
| L8 | 3 | I2 and (schottky near contact) with electrode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:14 |
| L9 | 0 | I2 and (schottky near contact) with electrode with (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:15 |
| L10 | 1 | I2 and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:15 |
| L11 | 1 | I2 and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:15 |
| L12 | 167 | (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:17 |

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| L13 | 0 | photodetecotr and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:18 |
| L14 | 4 | photodetector and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:18 |
| L15 | 1 | photodetector and (gan or nitride) and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:18 |
| L16 | 75 | (gan or nitride) and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:19 |
| L17 | 44 | (gan or (gallium near nitride)) and (schottky near contact) with electrode same (reverse or forward) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:19 |
| L18 | 162 | (gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:19 |
| L19 | 162 | (gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:20 |
| L20 | 69 | (gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward) same (bias or biasing or baied)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:20 |
| L21 | 83 | (gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward) same (bias or biasing or biased)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:20 |

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| L22 | 24 | (gan or (gallium near nitride)) and (schottky with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:22 |
| L23 | 18 | (gan or (gallium near nitride)).clm. and (schottky with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:24 |
| L24 | 0 | (gan or (gallium near nitride)).clm. and (schottky with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:24 |
| L25 | 0 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:24 |
| L26 | 2 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode same (reverse or forward) same (bias or biasing or biased) same (gan or (gallium adj nitride))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:24 |
| L27 | 27 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode with (gan or (gallium near nitride))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:25 |

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| L28 | 4 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode with (gan or (gallium near nitride))).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:25 |
| L29 | 34 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with electrode).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:26 |
| L30 | 1 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near2 between)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:27 |
| L31 | 25 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near2 between)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:27 |
| L32 | 30 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:27 |
| L33 | 3 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:28 |
| L34 | 30 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:29 |
| L35 | 0 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between) with ((high-resistivity) or resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:29 |

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| L36 | 0 | (gan or (gallium near nitride)).clm. and ((schottky near contact) with (electrode near5 between) same ((high-resistivity) or resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:29 |
| L37 | 1 | (gan or (gallium near nitride)).clm. and ((schottky near contact) same (electrode near5 between) same ((high-resistivity) or resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:30 |
| L38 | 398 | ((schottky near contact) with (electrode near5 between)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:30 |
| L39 | 1 | ((schottky near contact) with (electrode near5 between)) and ((high near resistivity) near2 ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:31 |
| L40 | 3 | ((schottky near contact) with (electrode near5 between)) and (((high near resistivity) or resistive or resistivity) near2 ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:31 |
| L41 | 3 | ((schottky near contact) with (electrode near5 between)) and (((highly or high) near resistivity) or resistive or resistivity) near2 ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:32 |
| L42 | 5 | ((schottky near contact) with (electrode near5 between) near5 ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:33 |

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| L43 | 44 | ((schottky near contact) with (electrode) near10 ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:33 |
| L44 | 56 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:34 |
| L45 | 16 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:38 |
| L46 | 2 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) same (leakage near current)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:39 |
| L47 | 3 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) and (leakage near current)).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:39 |
| L48 | 17 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) and (leakage near current)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:40 |
| L49 | 6 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) same (leakage near current)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:40 |
| L50 | 5 | ((schottky near contact) with (electrode) with ((gallium adj nitride) or gan) same (leakage near current) same reverse) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:41 |

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| L51 | 34373 | ((schottky near contact) near10 (electrode) near10 (gallium adj nitride) or gan) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:42 |
| L52 | 37 | ((schottky near contact) near10 (electrode) near10 ((gallium adj nitride) or gan)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:42 |
| L53 | 13 | ((schottky near contact) near10 (electrode) near10 ((gallium adj nitride) or gan)) and leakage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 16:42 |
| L54 | 98 | (US-20030218183-\$ or US-20030146444-\$ or US-20050012113-\$ or US-20020074553-\$ or US-20040080010-\$ or US-20030062525-\$ or US-20030015708-\$ or US-20020155634-\$ or US-20050167680-\$ or US-20060199289-\$ or US-20060226417-\$ or US-20050274964-\$ or US-20050082543-\$ or US-20050167697-\$ or US-20040124435-\$ or US-20030127658-\$ or US-20030071276-\$ or US-20020096687-\$ or US-20030214807-\$ or US-20030047744-\$ or US-20030122147-\$ or US-20070066020-\$ or US-20050194612-\$ or US-20060054925-\$ or US-20040144991-\$ or US-20080038856-\$).did. or (US-20070228415-\$ or US-20070194347-\$ or US-20070187666-\$ or US-20070170934-\$ or US-20070166888-\$ or US-20070147453-\$ or US-20070145390-\$ or US-20070085097-\$ or US-20070026552-\$ or US-20060226442-\$ or US-20060226415-\$ or US-20060223293-\$ or US- | US-PGPUB; USPAT; JPO; DERWENT | OR | ON | 2008/03/10 17:28 |

20050151255-\$ or US-
20050087766-\$ or US-
20050051804-\$ or US-
20040266043-\$ or US-
20040201038-\$ or US-
20040173751-\$ or US-
20040127042-\$ or US-
20030205721-\$ or US-
20030183921-\$ or US-
20020179932-\$ or US-
20020179914-\$ or US-
20020017696-\$ or US-
20010042860-\$ or US-
20010040247-\$ or US-
20010040246-\$).did.
or (US-6429467-\$ or
US-6208074-\$ or US-
5717235-\$ or US-
5977565-\$ or US-
5673220-\$ or US-
5932905-\$ or US-
5507881-\$ or US-
5707887-\$ or US-
5847397-\$ or US-
5677538-\$ or US-
5598014-\$ or US-
6586272-\$ or US-
6495852-\$ or US-
6455340-\$ or US-
7151281-\$ or US-
4696648-\$ or US-
4593304-\$ or US-
7002189-\$ or US-
7329908-\$ or US-
7285806-\$ or US-
7224004-\$ or US-
7205168-\$ or US-
7132699-\$ or US-
7071526-\$ or US-
6969873-\$ or US-
6965107-\$).did. or
(US-6890834-\$ or US-
6703649-\$ or US-
6593597-\$ or US-
6552373-\$ or US-
6492669-\$ or US-
6350999-\$ or US-
6064082-\$).did. or
(JP-06216404-\$ or JP-
01253286-\$ or JP-
2004228481-\$ or JP-
2003229566-\$ or JP-
2000223697-\$).did. or
(US-20050012113-\$
or US-20030230235-\$

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| | | or EP-296371-\$ or US-20050032345-\$ or JP-06216404-\$ or KR-587021-B-\$ or KR-609968-B-\$ or CN-1641327-\$ or US-20040080011-A-\$ or JP-2001185717-\$). did. | | | | |
| L55 | 69 | I54 and (schottky near contact)\ | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:28 |
| L56 | 69 | I54 and (schottky near contact) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:28 |
| L57 | 63 | I54 and ((schottky near contact) same (gan or (gallium near nitride))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:29 |
| L58 | 61 | I54 and ((schottky near contact) with (gan or (gallium near nitride))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:29 |
| L59 | 53 | I54 and ((schottky near contact) with (gan or (gallium near nitride)) with electrode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:29 |
| L60 | 5858 | schottky near barrier near diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:37 |
| L61 | 9 | I54 and schottky near barrier near diode | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:37 |
| L62 | 9 | I54 and ((schottky near barrier near diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:38 |

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| L63 | 99 | nucleation and ((schottky near barrier near diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:38 |
| L64 | 85 | nucleation and active and ((schottky near barrier near diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:38 |
| L65 | 13 | nucleation and active and (schottky near contact) and ((schottky near barrier near diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:38 |
| L66 | 230 | active and (schottky near contact) and ((schottky near barrier near diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:39 |
| L67 | 102 | active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (leakage near current) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:40 |
| L68 | 19 | active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (leakage near current) and (gan or (gallium near nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:40 |
| L69 | 36 | active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (gan or (gallium near nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:41 |
| L70 | 5 | active and (schottky near contact) and ((schottky near barrier near diode) or sbd) and (gan or (gallium near nitride)) and ((high or highly) near (resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:42 |

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| L71 | 10 | (schottky near contact) and ((schottky near barrier near diode) or sbd) and (gan or (gallium near nitride)) and ((high or highly) near (resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:42 |
| L72 | 45 | (schottky near contact) and ((schottky near2 diode) or sbd) and (gan or (gallium near nitride)) and ((high or highly) near (resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:43 |
| L73 | 29 | (schottky near contact) and ((schottky near2 diode) or sbd) and (gan or (gallium near nitride)).clm. and ((high or highly) near (resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:44 |
| L74 | 11 | (schottky near contact).clm. and ((schottky near2 diode) or sbd) and (gan or (gallium near nitride)).clm. and ((high or highly) near (resistive or resistivity)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:44 |
| L75 | 1676 | (schottky near2 diode) and (schottky near contact) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:45 |
| L76 | 273 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:45 |
| L77 | 222 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:45 |

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| L78 | 179 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 17:45 |
| L79 | 97 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near2 gallium)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:09 |
| L80 | 65 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near2 gallium)) and ((gan or gallium) with (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:10 |
| L81 | 85 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near2 gallium)) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:12 |

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| L82 | 87 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near5 gallium)) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:12 |
| L83 | 12 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and (AlInGaN or InAlGaN or (aluminum near5 gallium)) and ((gan or gallium) same (dope or doping or doped or dopant)) and nucleation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:12 |
| L84 | 17 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) and nucleation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:13 |

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| L85 | 134 | (schottky near2 diode) and (schottky near contact) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:21 |
| L86 | 139 | (schottky near2 diode) and (schottky adj (metal or contact)) and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:23 |
| L87 | 52 | (schottky near2 diode) and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact) and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:23 |
| L88 | 40 | (schottky near2 diode) and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:23 |

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| L89 | 20 | (schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:24 |
| L90 | 8 | (schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:25 |
| L91 | 4 | (schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and (resistive or resistivity) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:26 |

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| L92 | 8 | (schottky near2 diode).ti,ab,clm. and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and leakage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:26 |
| L93 | 9 | (schottky near2 diode) and (schottky adj (metal or contact)).clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and leakage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:28 |
| L94 | 10 | (schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact).clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).clm. and leakage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:29 |

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| L95 | 10 | (schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact). ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)). clm. and leakage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:29 |
| L96 | 10 | (schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact). ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).ti, ab,clm. and leakage | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:32 |
| L97 | 4 | (schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact). ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).ti, ab,clm. and leakage and electrode.ti,ab, clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:32 |

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|------|-------|---|---|----|----|---------------------|
| L98 | 1 | (schottky near2 diode) and (schottky adj (metal or contact)).ti,ab,clm. and (gan or (gallium near nitride)) and (ohmic near contact).ti,ab,clm. and ((active or semiconductor) near layer) and ((gan or gallium) same (dope or doping or doped or dopant)).ti,ab,clm. and leakage.ti,ab,clm. and electrode.ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:32 |
| L99 | 19710 | ((schottky near2 diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:34 |
| L100 | 2617 | ((schottky near2 diode) or sbd) and (ohmic near contact) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:35 |
| L101 | 935 | ((schottky near2 diode) or sbd) and (ohmic near contact) and (schottky adj (metal or contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:35 |
| L102 | 930 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:35 |
| L103 | 32 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and (aluminum near2 indium near2 gallium near2 nitride) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:35 |

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| L104 | 23 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and ((aluminum near2 indium near2 gallium near2 nitride) and alingan or inalgan) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:36 |
| L105 | 47 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and ((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:36 |
| L106 | 10 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (metal or contact)) and (((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) same schottky) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:37 |
| L107 | 5 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) same schottky) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:38 |
| L108 | 4 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (((aluminum near2 indium near2 gallium near2 nitride) or alingan or inalgan) same (schottky adj contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:38 |

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| L109 | 826 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:39 |
| L110 | 667 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (dope or doping or doped or dopant) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:39 |
| L111 | 34 | ((schottky near2 diode) or sbd) and (ohmic adj contact) and (schottky adj (contact)) and (dope or doping or doped or dopant) and nucleation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:39 |
| L112 | 17 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)) and (dope or doping or doped or dopant) and nucleation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:40 |
| L113 | 12 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant) and nucleation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:40 |
| L114 | 9 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and nucleation | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:40 |

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|------|-----|---|---|----|----|------------------|
| L115 | 135 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:40 |
| L116 | 49 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:51 |
| L117 | 47 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) same (schottky adj contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:57 |
| L118 | 44 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) same (schottky adj contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:58 |

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|------|-----|---|---|----|----|------------------|
| | | same (metal or electrode)) | | | | |
| L119 | 39 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) with (schottky adj contact) same (metal or electrode)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:58 |
| L120 | 30 | ((schottky near2 diode) or sbd) and (ohmic adj contact).ti, ab,clm. and (schottky adj (contact)).ti,ab, clm. and (dope or doping or doped or dopant).ti,ab,clm. and ((schottky near contact) same (bias or biased or biasing or voltage) same (reverse or forward)) and ((ohmic adj contact) with (schottky adj contact) with (metal or electrode)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 18:58 |
| L121 | 105 | (US-20030218183-\$ or US-20030146444-\$ or US-20050012113-\$ or US-20020074553-\$ or US-20040080010-\$ or US-20030062525-\$ or US-20030015708-\$ or US-20020155634-\$ or US-20050167680-\$ or US-20060199289-\$ or US-20060226417-\$ or US-20050274964-\$ or US-20050082543-\$ or US-20050167697-\$ or US-20040124435-\$ or US-20030127658-\$ | US-PGPUB; USPAT; JPO; DERWENT | OR | ON | 2008/03/10 19:01 |

or US-20030071276-\$
or US-20020096687-\$
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| | | 6495852-\$ or US- 6455340-\$ or US- 7151281-\$ or US- 4696648-\$ or US- 4593304-\$ or US- 7002189-\$ or US- 7329908-\$ or US- 7285806-\$ or US- 7224004-\$ or US- 7205168-\$ or US- 7132699-\$ or US- 7071526-\$ or US- 6969873-\$ or US- 6965107-\$).did. or (US-6890834-\$ or US- 6703649-\$ or US- 6593597-\$ or US- 6552373-\$ or US- 6492669-\$ or US- 6350999-\$ or US- 6064082-\$ or US- 7229866-\$ or US- 7115896-\$ or US- 7253015-\$).did. or (JP-06216404-\$ or JP- 01253286-\$ or JP- 2004228481-\$ or JP- 2003229566-\$ or JP- 2000223697-\$).did. or (US-20050012113-\$ or US-20030230235-\$ or EP-296371-\$ or US- 20050032345-\$ or JP- 06216404-\$ or KR- 587021-B-\$ or KR- 609968-B-\$ or CN- 1641327-\$ or US- 20040080011-A-\$ or JP-2001185717-\$ or WO-03094240-A-\$). did. | | | | |
| L122 | 4 | l121 and (schottky near contact) near2 between | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:02 |
| L123 | 9 | l121 and (schottky near contact) near5 between | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:03 |

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|------|------|---|---|----|----|---------------------|
| L124 | 76 | l121 and (schottky near contact) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:11 |
| L125 | 33 | l121 and ((form or forming or formed or formation) near2 (schottky near contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:12 |
| L126 | 41 | l121 and ((form or forming or formed or formation) near5 (schottky near contact)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:14 |
| L127 | 3616 | 257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:44 |
| L128 | 103 | l127 and (schottky near2 diode) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:44 |
| L129 | 103 | l127 and ((schottky near2 diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:44 |
| L130 | 5056 | 257/184.ccls. or 257/190.ccls. or 257/452.ccls. or 257/457.ccls. or 257/459.ccls. or 257/461.ccls. or 257/194.ccls. or 438/604.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:45 |
| L131 | 166 | l130 and ((schottky near2 diode) or sbd) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/10 19:45 |

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